

FEATURES

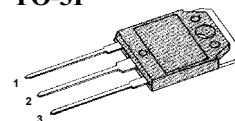
- Avalanche Rugged Technology
- Rugged Gate Oxide Technology
- Lower Input Capacitance
- Improved Gate Charge
- Extended Safe Operating Area
- Lower Leakage Current : 10 μ A (Max.) @ $V_{DS} = 400V$
- Low $R_{DS(on)}$: 0.254 Ω (Typ.)

$$BV_{DSS} = 400 V$$

$$R_{DS(on)} = 0.3 \Omega$$

$$I_D = 17 A$$

TO-3P



1.Gate 2. Drain 3. Source

Absolute Maximum Ratings

Symbol	Characteristic	Value	Units
V_{DSS}	Drain-to-Source Voltage	400	V
I_D	Continuous Drain Current ($T_C=25^\circ C$)	17	A
	Continuous Drain Current ($T_C=100^\circ C$)	10.8	
I_{DM}	Drain Current-Pulsed ①	68	A
V_{GS}	Gate-to-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy ②	1156	mJ
I_{AR}	Avalanche Current ①	17	A
E_{AR}	Repetitive Avalanche Energy ①	20.2	mJ
dv/dt	Peak Diode Recovery dv/dt ③	4.0	V/ns
P_D	Total Power Dissipation ($T_C=25^\circ C$)	202	W
	Linear Derating Factor	1.61	W/ $^\circ C$
T_J, T_{STG}	Operating Junction and Storage Temperature Range	- 55 to +150	$^\circ C$
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5-seconds	300	

Thermal Resistance

Symbol	Characteristic	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	--	0.62	$^\circ C / W$
$R_{\theta CS}$	Case-to-Sink	0.24	--	
$R_{\theta JA}$	Junction-to-Ambient	--	40	

IRFP350A

N-CHANNEL POWER MOSFET

Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
BV_{DSS}	Drain-Source Breakdown Voltage	400	--	--	V	$V_{GS}=0V, I_D=250\ \mu A$
$\Delta BV/\Delta T_J$	Breakdown Voltage Temp. Coeff.	--	0.46	--	V/°C	$I_D=250\ \mu A$ See Fig 7
$V_{GS(th)}$	Gate Threshold Voltage	2.0	--	4.0	V	$V_{DS}=5V, I_D=250\ \mu A$
I_{GSS}	Gate-Source Leakage, Forward	--	--	100	nA	$V_{GS}=30V$
	Gate-Source Leakage, Reverse	--	--	-100		$V_{GS}=-30V$
I_{DSS}	Drain-to-Source Leakage Current	--	--	10	μA	$V_{DS}=400V$
		--	--	100		$V_{DS}=320V, T_C=125^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-State Resistance	--	--	0.3	Ω	$V_{GS}=10V, I_D=8.5A$ ④
g_{fs}	Forward Transconductance	--	11.65	--	S	$V_{DS}=50V, I_D=8.5A$ ④
C_{iss}	Input Capacitance	--	2140	2780	pF	$V_{GS}=0V, V_{DS}=25V, f=1\text{MHz}$ See Fig 5
C_{oss}	Output Capacitance	--	305	350		
C_{rss}	Reverse Transfer Capacitance	--	134	155		
$t_{d(on)}$	Turn-On Delay Time	--	20	50	ns	$V_{DD}=200V, I_D=17A,$ $R_G=6.2\ \Omega$ See Fig 13 ④⑤
t_r	Rise Time	--	22	55		
$t_{d(off)}$	Turn-Off Delay Time	--	100	210		
t_f	Fall Time	--	32	75		
Q_g	Total Gate Charge	--	101	131	nC	$V_{DS}=320V, V_{GS}=10V,$ $I_D=17A$ See Fig 6 & Fig 12 ④⑤
Q_{gs}	Gate-Source Charge	--	14	--		
Q_{gd}	Gate-Drain("Miller") Charge	--	51.5	--		

Source-Drain Diode Ratings and Characteristics

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
I_S	Continuous Source Current	--	--	17	A	Integral reverse pn-diode in the MOSFET
I_{SM}	Pulsed-Source Current ①	--	--	68		
V_{SD}	Diode Forward Voltage ④	--	--	1.5	V	$T_J=25^\circ\text{C}, I_S=17A, V_{GS}=0V$
t_{rr}	Reverse Recovery Time	--	385	--	ns	$T_J=25^\circ\text{C}, I_F=17A$
Q_{rr}	Reverse Recovery Charge	--	4.85	--	μC	$di_F/dt=100A/\mu s$ ④

Notes ;

① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature

② $L=7\text{mH}, I_{AS}=17A, V_{DD}=50V, R_G=27\ \Omega$, Starting $T_J=25^\circ\text{C}$

③ $I_{SD} \leq 17A, di/dt \leq 250A/\mu s, V_{DD} \leq BV_{DSS}$, Starting $T_J=25^\circ\text{C}$

④ Pulse Test : Pulse Width = 250 μs , Duty Cycle $\leq 2\%$

⑤ Essentially Independent of Operating Temperature

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Fig 1. Output Characteristics

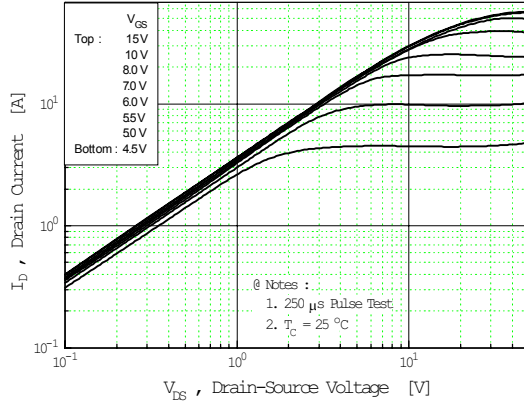


Fig 2. Transfer Characteristics

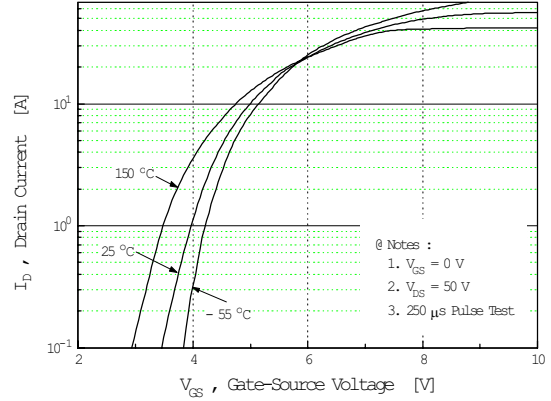


Fig 3. On-Resistance vs. Drain Current

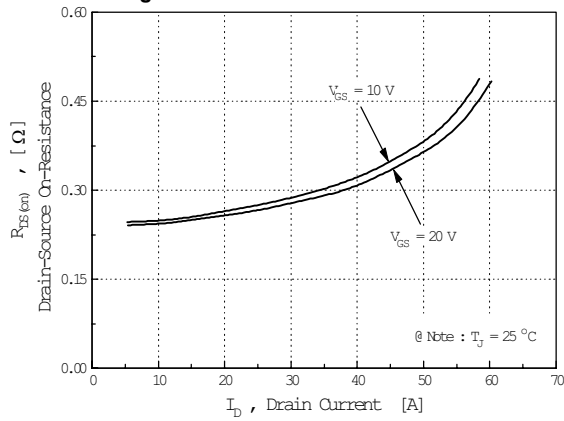


Fig 4. Source-Drain Diode Forward Voltage

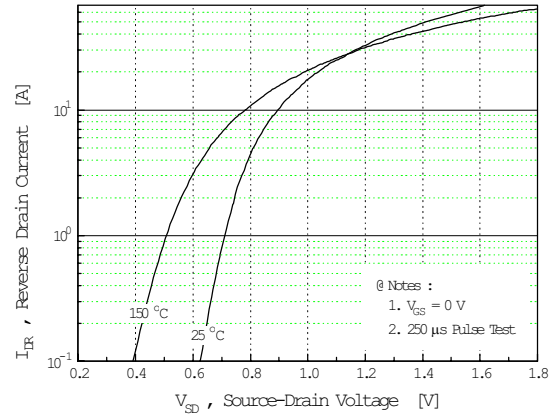


Fig 5. Capacitance vs. Drain-Source Voltage

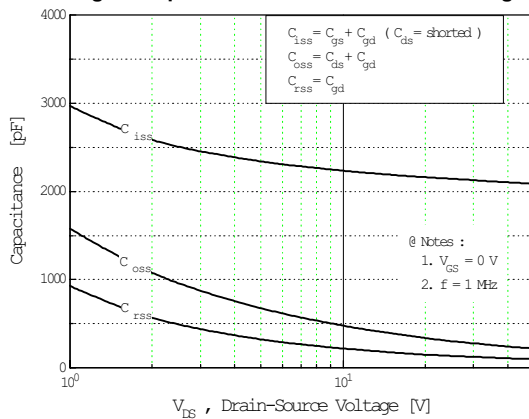
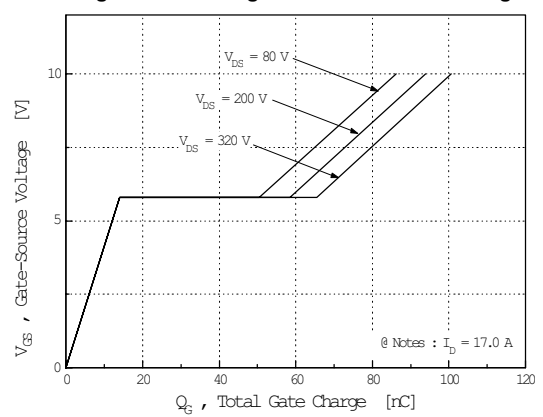


Fig 6. Gate Charge vs. Gate-Source Voltage



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Fig 7. Breakdown Voltage vs. Temperature

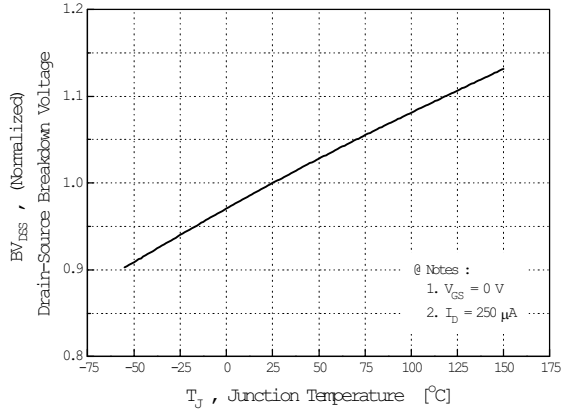


Fig 8. On-Resistance vs. Temperature

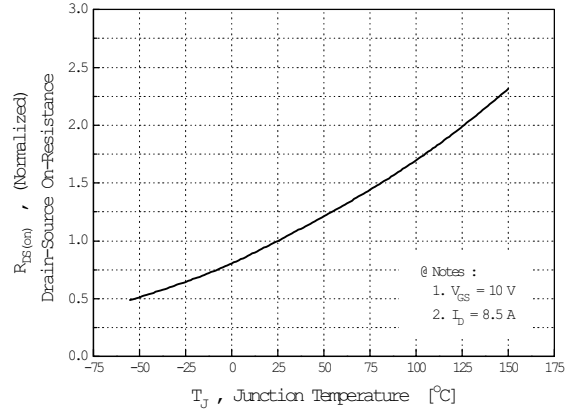


Fig 9. Max. Safe Operating Area

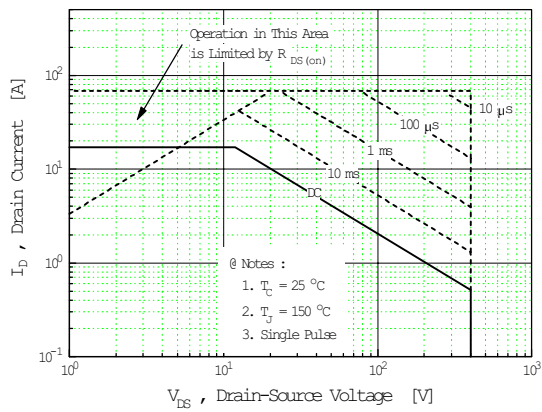


Fig 10. Max. Drain Current vs. Case Temperature

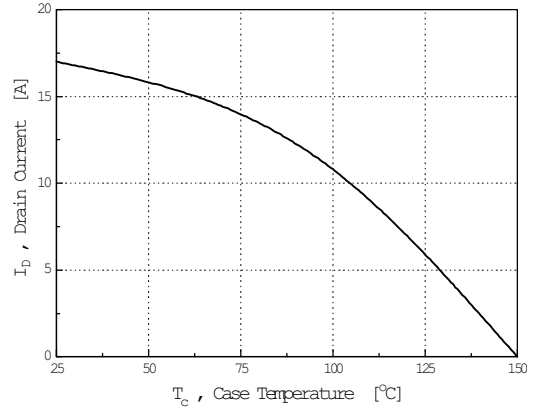
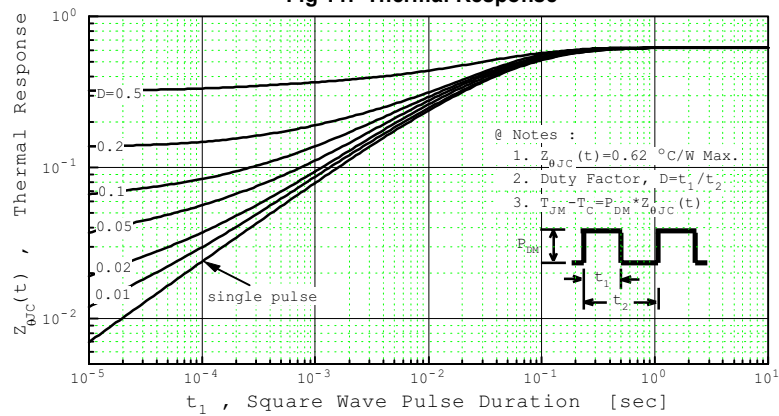


Fig 11. Thermal Response



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Fig 12. Gate Charge Test Circuit & Waveform

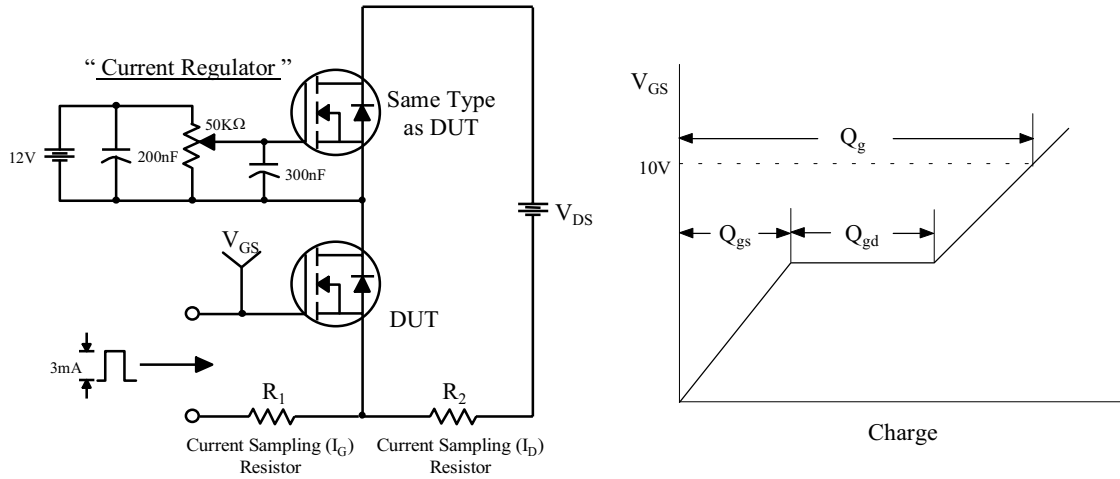


Fig 13. Resistive Switching Test Circuit & Waveforms

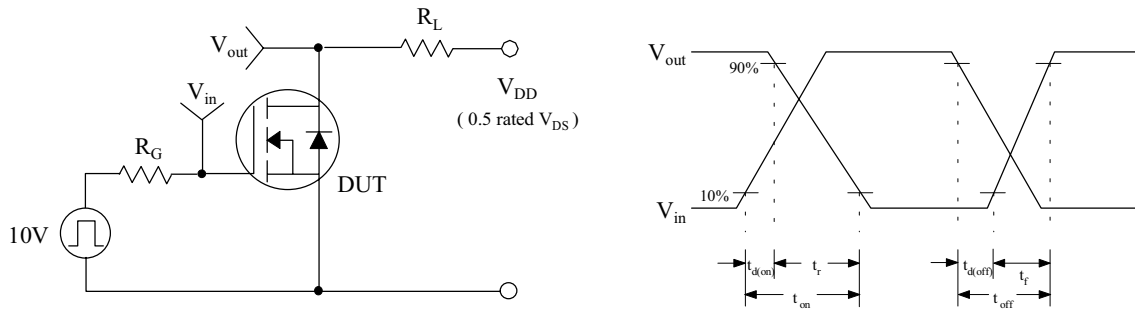
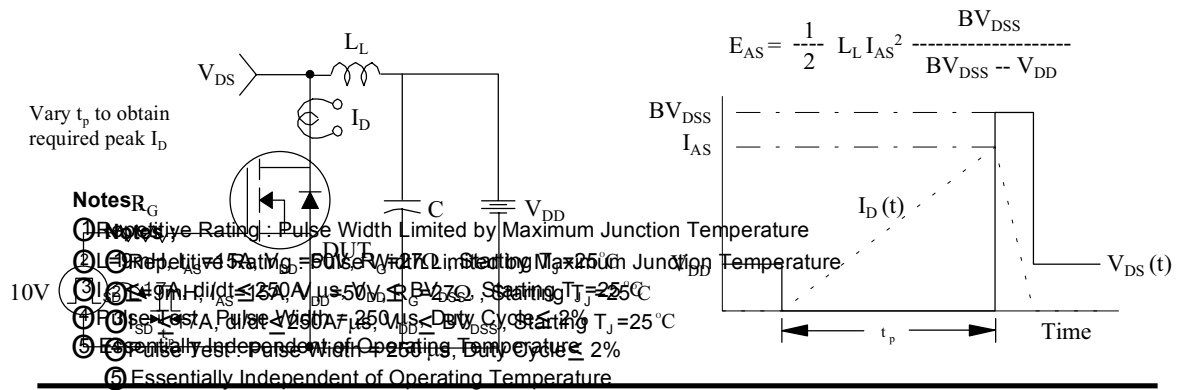


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms



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• dv/dt controlled by “ R_G ”

• I_S controlled by Duty Factor “ D ”

